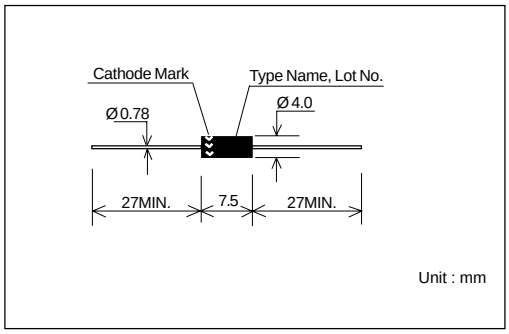
ESJC35-08 (8.0kV/410mA)

HIGH VOLTEGE DIODE

ESJC35 is high reliability resin molded type high voltage diode in small size package which is sealed a multilayed mesa type silicon chip by epoxy resin.

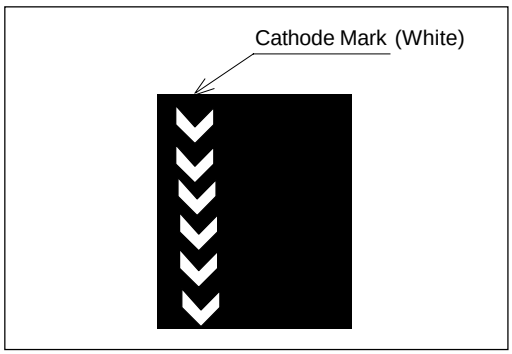
Outline Drawings



Features

- Low V_F
- High reliability .
- High speed switching

Cathode Mark



Applications

- Rectification for X-ray generator high voltage power supply

Maximum Ratings and Characteristics

- Absolute Maximum Ratings

Items	Symbols	Conditions	ESJC35-08	Units
Repetitive Peak Reverse Voltage	V_{RRM}		8.0	kV
Average Forward Current	Io	Toil=25°C, Resistive Load	410	mA
Non-repetitive Peak Forward Current	I_{FSM}	50Hz.sine harf-wave peak value. One-shot.Ta=25°C	10	A
Allowable Junction Temperature	T_j		120	°C
Storage Temperature Range	Tstg		-40 to +120	°C

- Electrical Characteristics (Ta=25°C Unless otherwise specified)

Items	Symbols	Conditions	ESJC35-08	Units
Maximum Forward Voltage Drop	V_F	at 25°C, I_F=1A	20	V
Maximum Reverse Current	I_{R1}	at 25°C, VR=8.0kV	2	μA
	I_{R2}	at 100°C, VR=8.0kV	10	
Minimum Reverse Recovery Time	trr	at 25°C, IF=IR=100mA 90%Recovery	0.15	μs

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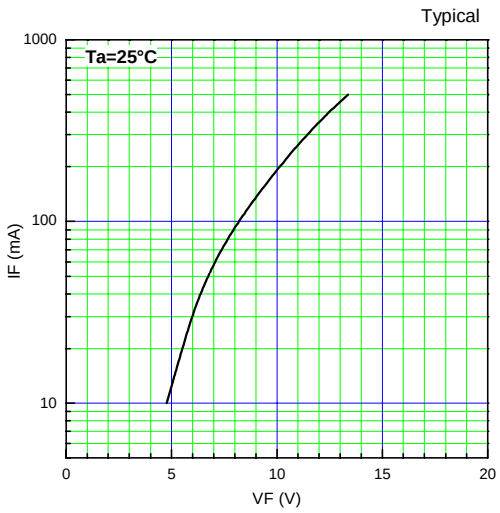
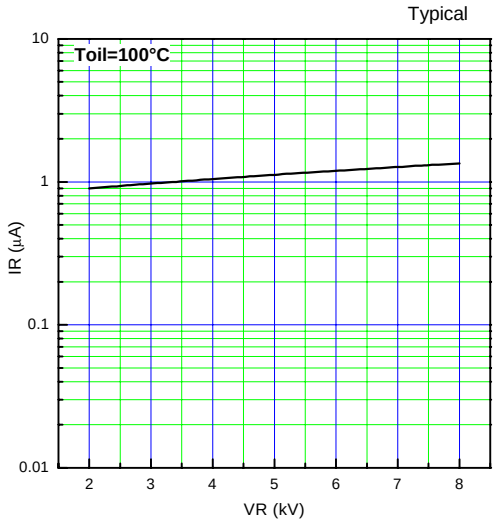
■ Characteristics

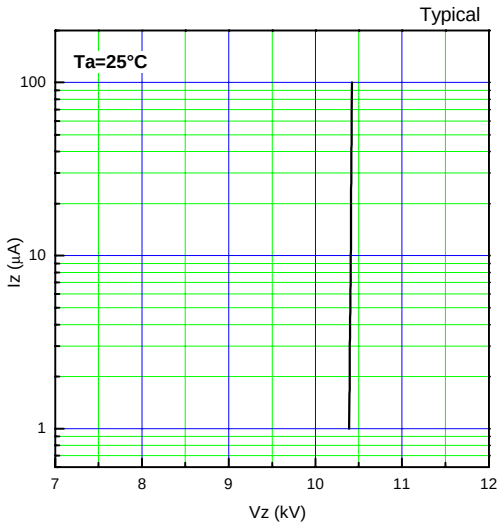
Forward characteristic [VF-IF]



Reverse characteristic [VR-IR]



Avalanche characteristic [Vz-Iz]



Reverse recovery time characteristic [Ta-trr]